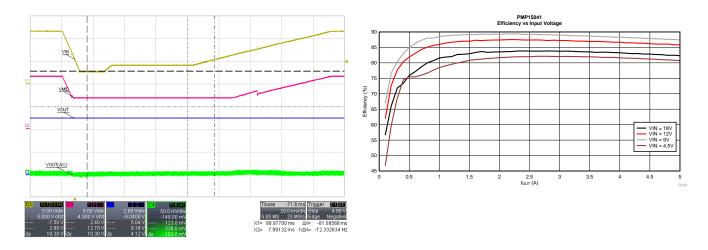
Test Report: TIDT001 25-W, Automotive, Start-Stop Reference Design Operating at 2.2 MHz



Description

Automotive 12-V batteries typically operate in the range of 9 V to 16 V. However, this voltage can vary widely due to transient conditions such as cold crank and load dump. This reference design creates a well regulated 25-W (5-V, 5-A) output, regardless of large input voltage transients, by using the LM5150-Q1 and LM5141-Q1 controllers. The LM5150-Q1 is implemented as a pre-boost, only switching when the input voltage is below 6.8 V. When the pre-boost stage is in bypass mode and not switching, the boost inductor is used as a differential mode EMI filter. The LM5141-Q1 operates as a buck controller to regulate the 5-V output. A switching frequency of 2.2 MHz is selected to help minimize the component size and avoid electromagnetic interference in the medium-wave frequency band (0.53 MHz to 1.8 MHz) and short-wave frequency band (5.9 MHz to 6.2 MHz). This test report discusses a number of design considerations and presents test results and waveforms from a demonstration board to a specific design requirement.



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1



1 System Parameters

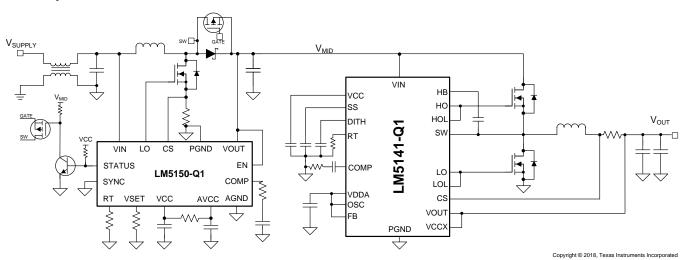


Figure 1. System Block Diagram

1.1 Voltage and Current Requirements

Table 1. Voltage and Current Requirements

PARAMETER	SPECIFICATIONS
V _{IN} (DC range)	4.5 V to 18 V (5-V start-up)
V _{IN} (transient range)	2.8 V to 40 V
V _{OUT}	5 V, 5 A (peak), 3 A (continuous)
Nominal switching frequency	LM5150: 2.2 MHz, LM5141: 2.2 MHz

1.2 Required Test Equipment

- Power supply
- Electronic load
- Oscilloscope

1.3 Design Considerations

1.3.1 Switching Frequency

2

Selecting a switching frequency of 2.2 MHz for the both the LM5150-Q1 and the LM5141-Q1 provides a number of benefits when comparing to lower switching frequencies. Component size is reduced, resulting in a smaller solution size and increasing power density. The control loop bandwidth can be increased to higher frequencies, resulting in a faster load transient response. In applications such as automotive radios, the switching frequency is selected to avoid generating noise in the reserved medium-wave frequency band (0.53 MHz to 1.8 MHz) and short-wave frequency band (5.9 MHz to 6.2 MHz). The fundamental frequency (2.2 MHz) and all harmonic frequencies lie outside of the reserved frequency bands, mitigating the effective electrical magnetic interference (EMI) in reserved frequency bands.

25-W, Automotive, Start-Stop Reference Design Operating at 2.2 MHz



1.3.2 Bypass P-Channel MOSFET

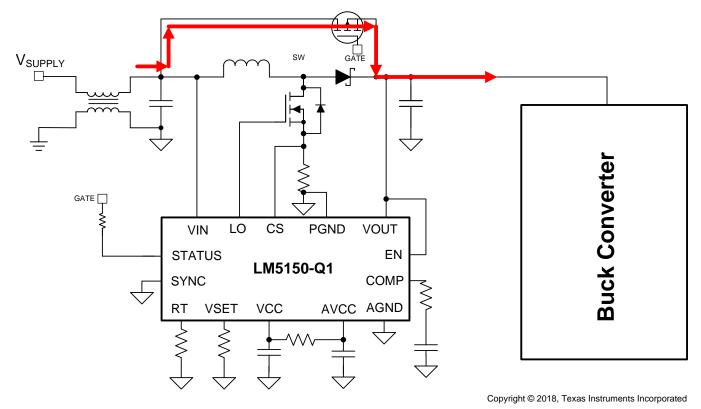


Figure 2. Boost Bypass Switch

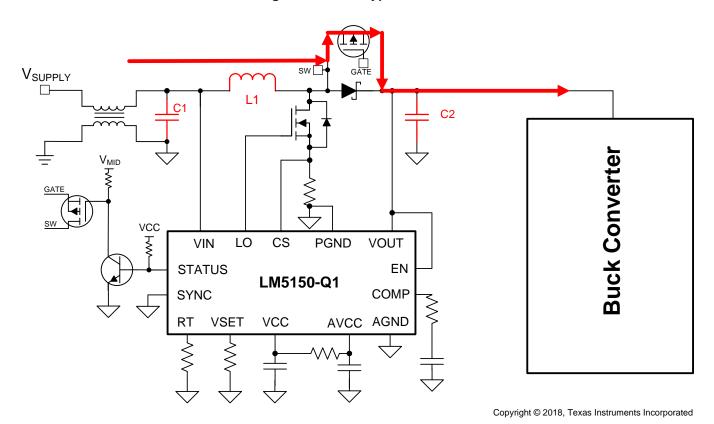


Figure 3. Diode Bypass Switch

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System Parameters

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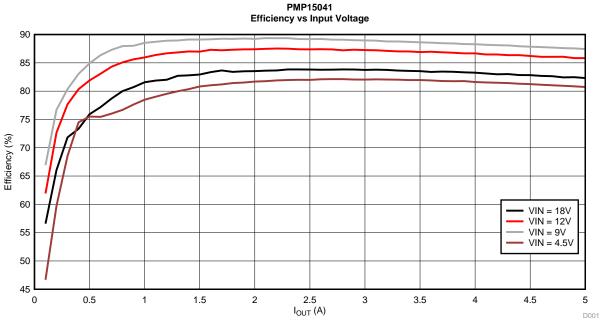
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The STATUS pin of the LM5150-Q1 is used to implement a bypass MOSFET. The bypass MOSFET is only enabled when the LM5150-Q1 is not operating. For details on the STATUS pin, see LM5150-Q1 Wide VIN Automotive Low IQ Boost Controller. Typically, this MOSFET is implemented to short out (bypass) the entirety of boost circuit. Figure 2 shows the typical implementation of the bypass switch. Bypassing the entire boost circuit increases the efficiency by eliminating the diode voltage drop and inductor's series resistance. Figure 3 shows the bypass switch only shorting out the diode. Shorting out the diode helps increase the efficiency but also allows for the boost inductor (L1) to form a differential EMI filter. C1, C2, and L1 in Figure 3 forms the differential EMI filter. Using L1 as a differential mode choke eliminates the need for adding an extra choke for EMI mitigation.

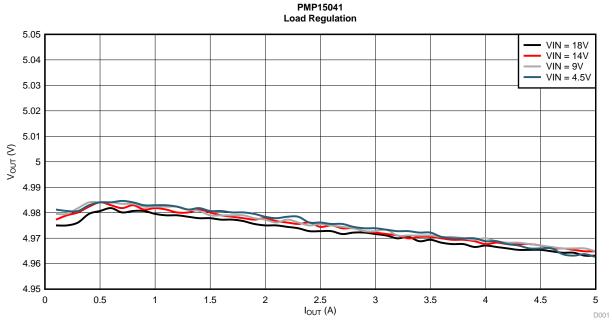


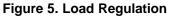
2 Testing and Results

2.1 Performance Graphs









Testing and Results

Testing and Results

2.2 Efficiency Data

Table 2. Efficiency Data (V_{IN} = 18 V)

V _{IN} (V)	I _{IN} (A)	V _{out} (V)	I _{оυт} (А)	EFFICIENCY (%)
18.007	0.159	4.980	0.421	73.351
18.007	0.348	4.980	1.025	81.572
18.001	0.476	4.978	1.425	82.795
18.012	0.671	4.975	2.029	83.533
18.007	0.801	4.973	2.432	83.839
18.007	1.001	4.972	3.035	83.747
18.007	1.135	4.969	3.438	83.577
18.012	1.339	4.967	4.041	83.262
18.012	1.479	4.965	4.444	82.837
18.001	1.690	4.963	5.045	82.310

Table 3. Efficiency Data (V_{IN} = 14 V)

V _{IN} (V)	I _{IN} (A)	V _{оит} (V)	I _{оυт} (А)	EFFICIENCY (%)
13.995	0.194	4.982	0.425	77.805
13.990	0.433	4.982	1.028	84.465
13.995	0.595	4.981	1.428	85.408
13.990	0.838	4.978	2.030	86.240
13.995	1.002	4.976	2.433	86.370
13.984	1.252	4.972	3.035	86.219
13.995	1.422	4.971	3.437	85.848
14.001	1.679	4.968	4.041	85.388
13.990	1.853	4.968	4.444	85.148
13.990	2.117	4.965	5.046	84.587

Table 4. Efficiency Data ($V_{IN} = 9 V$)

V _{IN} (V)	I _{IN} (A)	V _{оит} (V)	I _{оит} (А)	EFFICIENCY (%)
9.002	0.283	4.984	0.424	83.046
9.002	0.642	4.982	1.026	88.532
9.002	0.887	4.981	1.429	89.119
9.002	1.258	4.977	2.030	89.234
9.002	1.508	4.975	2.434	89.207
9.002	1.886	4.973	3.036	88.961
9.002	2.141	4.971	3.439	88.705
9.002	2.527	4.970	4.041	88.287
9.002	2.789	4.968	4.444	87.934
9.002	3.183	4.965	5.045	87.426

Table 5. Efficiency Data (V_{IN} = 4.5 V)

V _{IN} (V)	I _{IN} (A)	V _{OUT} (V)	I _{оит} (А)	EFFICIENCY (%)
4.509	0.628	4.983	0.423	74.494
4.509	1.447	4.983	1.028	78.487
4.510	1.963	4.982	1.428	80.351
4.509	2.745	4.978	2.031	81.690

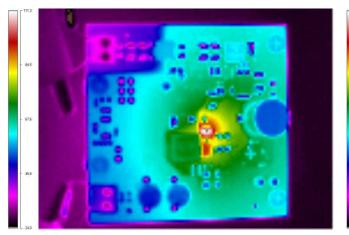
6 25-W, Automotive, Start-Stop Reference Design Operating at 2.2 MHz

V _{IN} (V)	I _{IN} (A)	V _{out} (V)	I _{оυт} (А)	EFFICIENCY (%)
4.508	3.276	4.976	2.434	82.001
4.509	4.081	4.974	3.035	82.039
4.509	4.627	4.972	3.439	81.959
4.508	5.457	4.969	4.041	81.612
4.508	6.021	4.966	4.444	81.306
4.508	6.881	4.963	5.046	80.728

Table 5. Efficiency Data (V_{IN} = 4.5 V) (continued)

2.3 Thermal Images

Figure 6 and Figure 7 show the temperature of the evaluation board with V_{IN} at 12 V and a continuous load of 5 A. The maximum continuous load is 3 A, which results in lower temperatures. The hottest location is the high-side MOSFET of the LM5141. The temperature of this component can be reduced by increasing the copper thickness or the copper area around the high-side MOSFET.



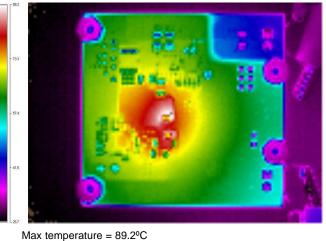


Figure 7. Rear Side: $V_{IN} = 12 V$, $I_{OUT} = 5 A$

Max temperature = 111.3° C Figure 6. Front Side: V_{IN} = 12 V, I_{out} = 5 A

2.4 Dimensions

The evaluation board dimensions are 2.2 in \times 2.1 in.

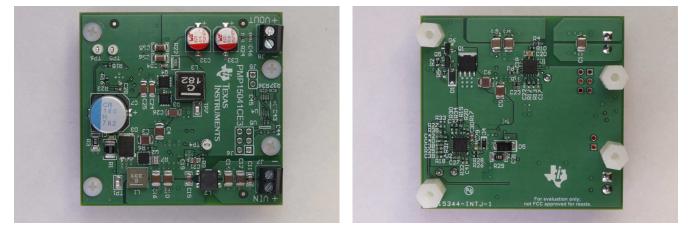


Figure 8. Front of Evaluation Board

Figure 9. Rear of Evaluation Board

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Waveforms

3 Waveforms

3.1 Input Voltage Transients

Figure 10 through Figure 11 show the response to a cold crank input voltage transient. The minimum voltage on the input terminals is 2.8 V.

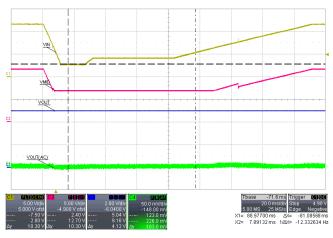


Figure 10. Input Voltage Transient Response

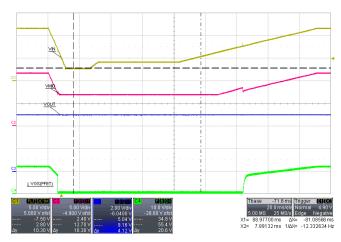
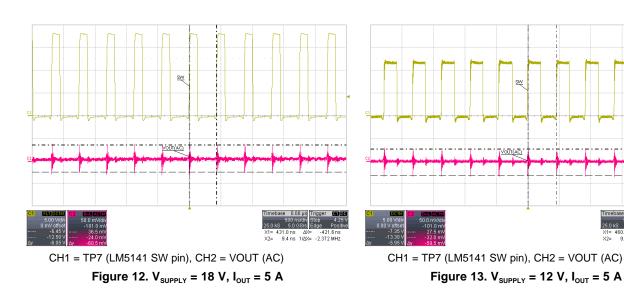


Figure 11. Input Voltage Transient Response (Bypass MOSFET)



25-W, Automotive, Start-Stop Reference Design Operating at 2.2 MHz

3.2 Output Voltage Ripple

X1= 460.6 ns ∆X= -451.2 ns X2= 9.4 ns 1/∆X= -2.2163 MHz



Waveforms

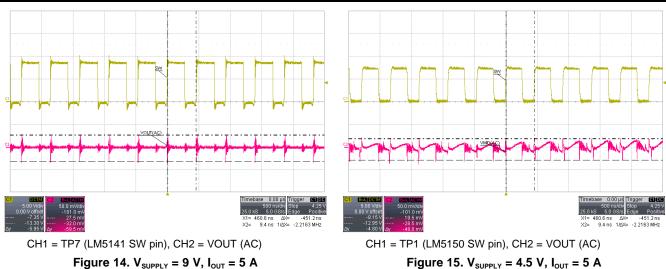


Figure 15. $V_{\text{SUPPLY}} = 4.5 \text{ V}, I_{\text{OUT}} = 5 \text{ A}$

Short Circuit Recovery 3.3

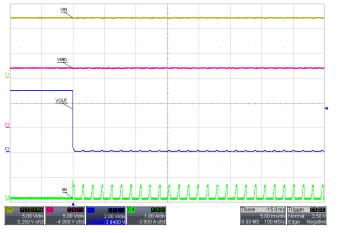


Figure 16. V_{IN} = 12 V, Short Circuit

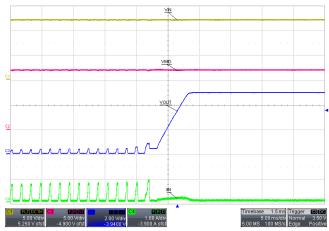
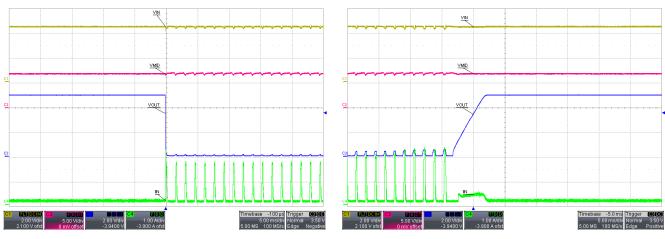
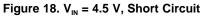
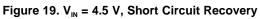


Figure 17. V_{IN} = 12 V, Short Circuit Recovery









Waveforms

Load Transients 3.4

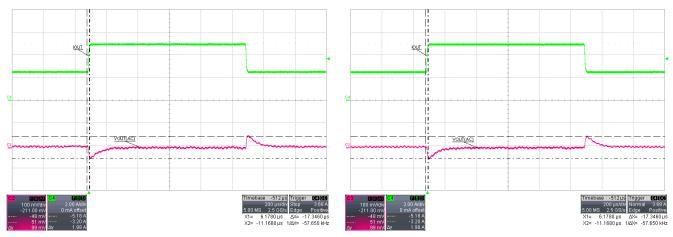


Figure 20. V_{\rm IN} = 18 V, I_{\rm OUT} = 2.5 A to 5 A

Figure 21. V_{IN} = 12 V, I_{OUT} = 2.5 A to 5 A

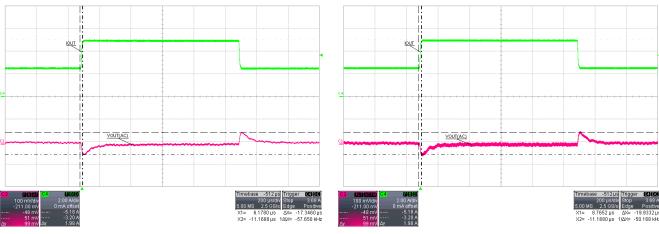


Figure 22. V_{IN} = 9 V, I_{OUT} = 2.5 A to 5 A

Figure 23. V_{IN} = 4.5 V, I_{OUT} = 2.5 A to 5 A

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3.5 Start-up Sequence

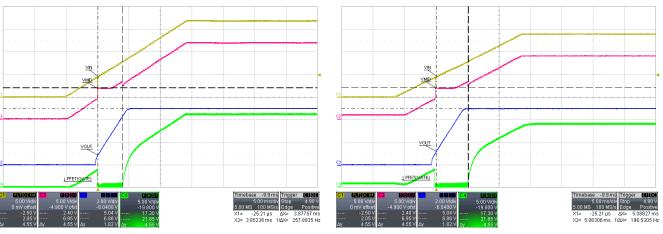


Figure 24. V_{IN} = 18 V, I_{OUT} = 5 A

Figure 25. V_{IN} = 14 V, I_{OUT} = 5 A

Waveforms

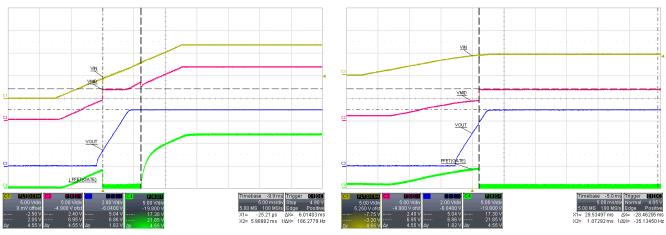
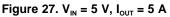
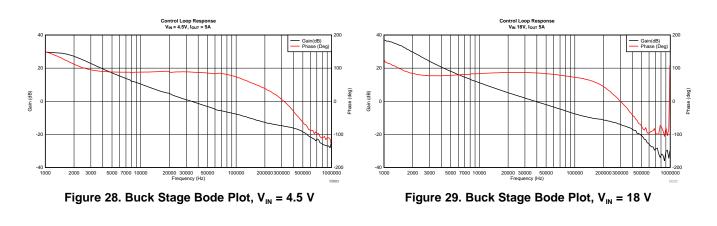


Figure 26. V_{IN} = 12 V, I_{OUT} = 5 A



3.6 Bode Plot

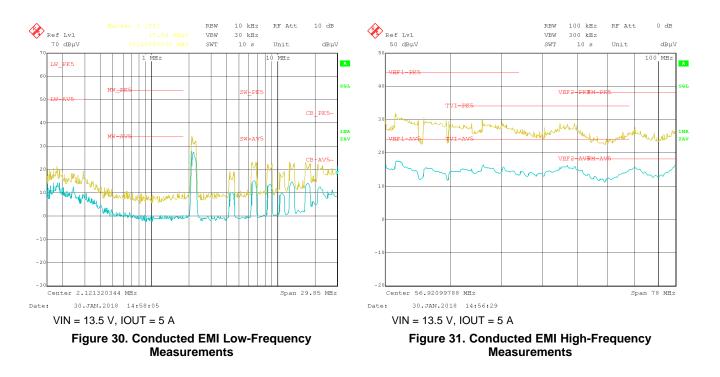




Waveforms

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3.7 EMI Performance



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